

## Product Summary

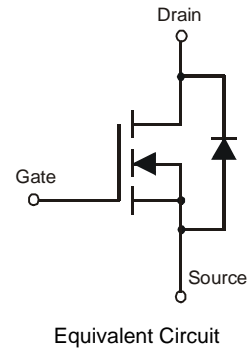
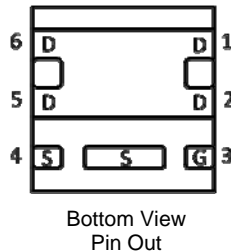
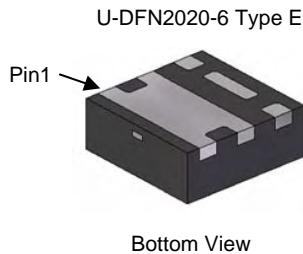
$V_{(BR)DSS}$	$R_{DS(ON) \max}$	Package	$I_{D \max}$ $T_A = +25^\circ\text{C}$
20V	11.6m $\Omega$ @ $V_{GS} = 4.5\text{V}$	U-DFN2020-6 Type E	10.5A
	15m $\Omega$ @ $V_{GS} = 2.5\text{V}$		9.4A

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- General Purpose Interfacing Switch
- Power Management Functions



## Features

- 0.6mm profile – ideal for low profile applications
- PCB footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

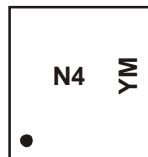
- Case: U-DFN2020-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (approximate)

## Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per reel
DMN2015UFDE-7	N4	7	3,000
DMN2015UFDE-13	N4	13	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



N4 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: Y = 2011)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	10.5 8.5	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	12.5 10.0	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = 2.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	9.4 7.5	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	11.2 8.8	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)		I <sub>DM</sub>	80	A
Maximum Body Diode Continuous Current		I <sub>S</sub>	2.5	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.66	W
	T <sub>A</sub> = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>θJA</sub>	189	°C/W
	t < 10s		132	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.03	W
	T <sub>A</sub> = +70°C		1.31	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>θJA</sub>	61	°C/W
	t < 10s		43	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	9.3	°C
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	9.3	11.6	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.5A
			11.4	15		
			17	30		
			24	50		
			24	50		
Forward Transfer Admittance	Y <sub>fs</sub>	—	11.3	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 8.5A
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 8.5A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	1779	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	175	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	154	—	pF	
Gate Resistance	R <sub>g</sub>	—	0.94	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	19.7	—	nC	
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	45.6	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	2.9	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.8	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	7.4	—	ns	
Turn-On Rise Time	t <sub>r</sub>	—	16.8	—	ns	V <sub>DS</sub> = 10V, I <sub>D</sub> = 8.5A V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 1.8Ω
Turn-Off Delay Time	t <sub>D(off)</sub>	—	43.6	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	10.9	—	ns	
Reverse Recovery Time	T <sub>rr</sub>	—	8.6	—	ns	I <sub>F</sub> = 8.5A, di/dt = 210A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	3.7	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

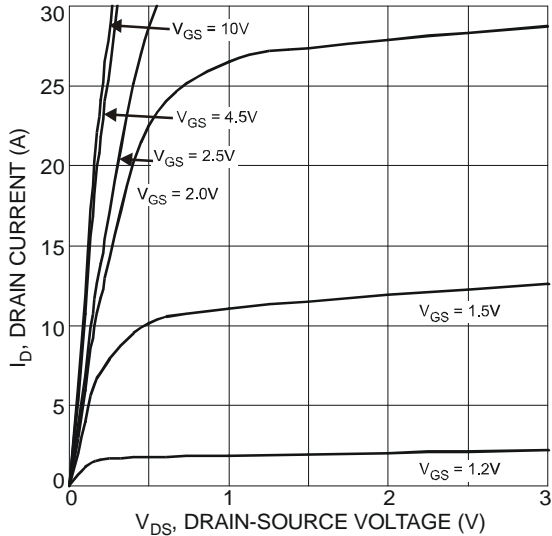


Fig. 1 Typical Output Characteristic

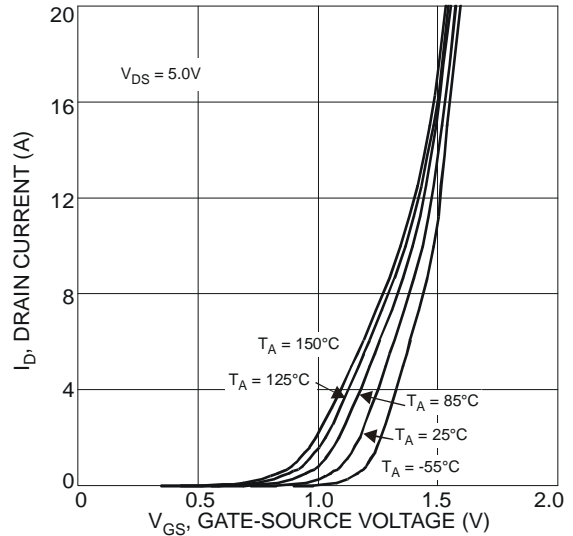


Fig. 2 Typical Transfer Characteristics

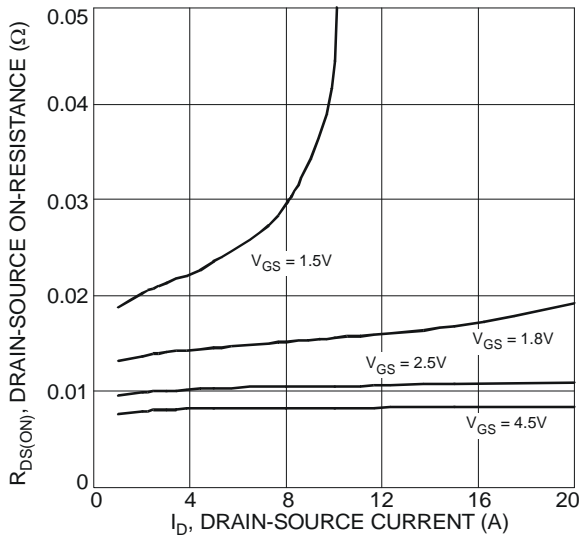


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

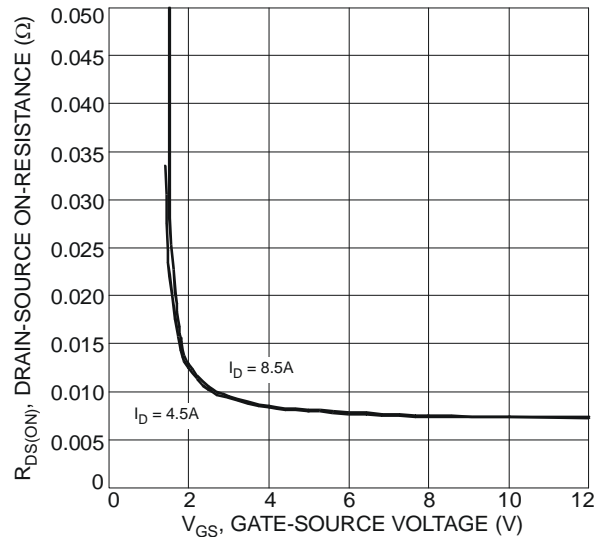


Fig. 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

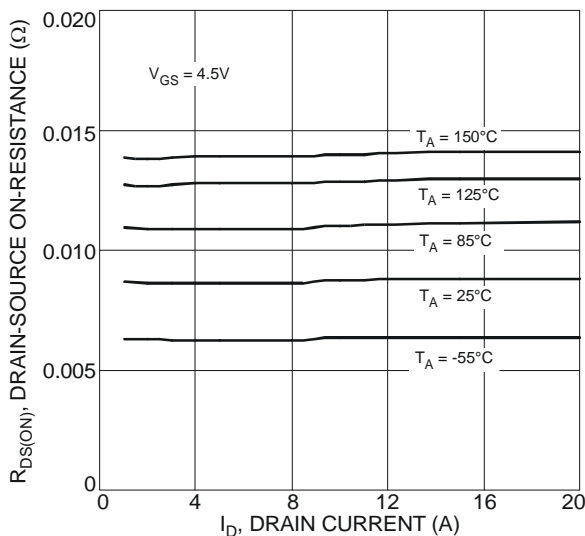


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

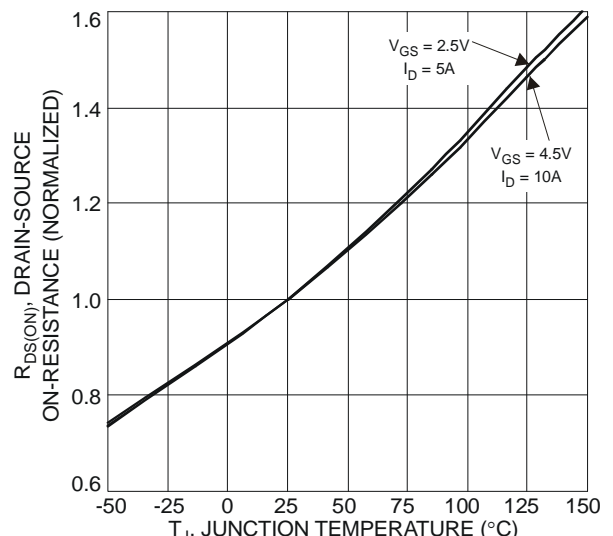


Fig. 6 On-Resistance Variation with Temperature

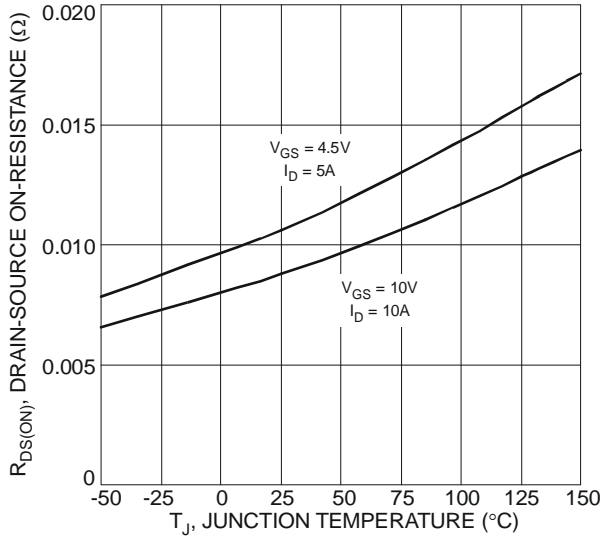


Fig. 7 On-Resistance Variation with Temperature

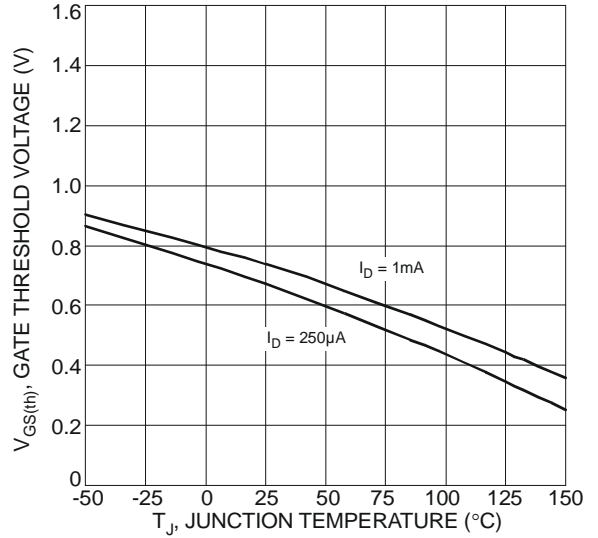


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

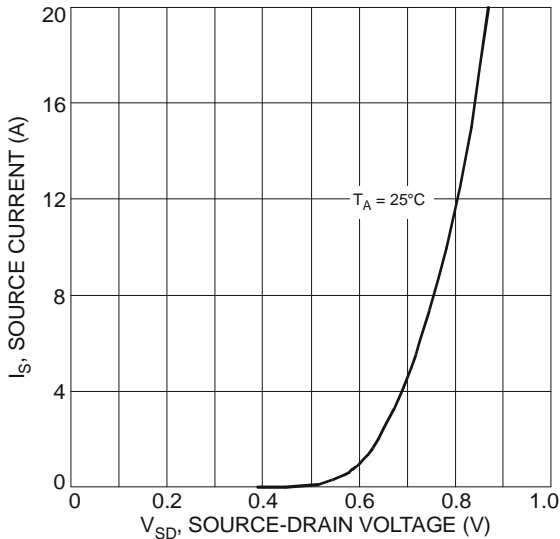


Fig. 9 Diode Forward Voltage vs. Current

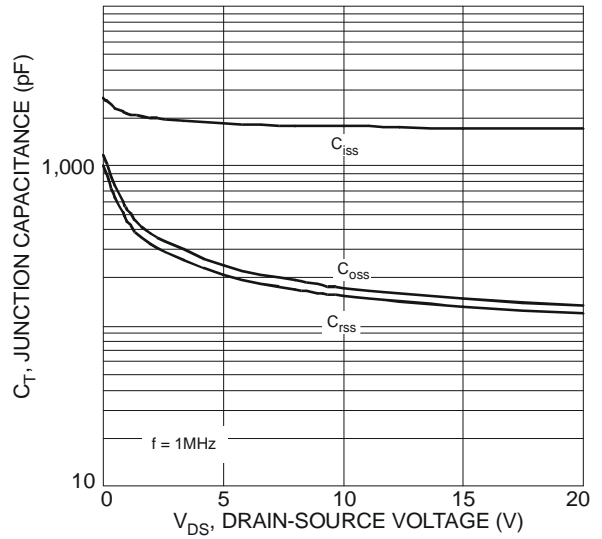


Fig. 10 Typical Junction Capacitance

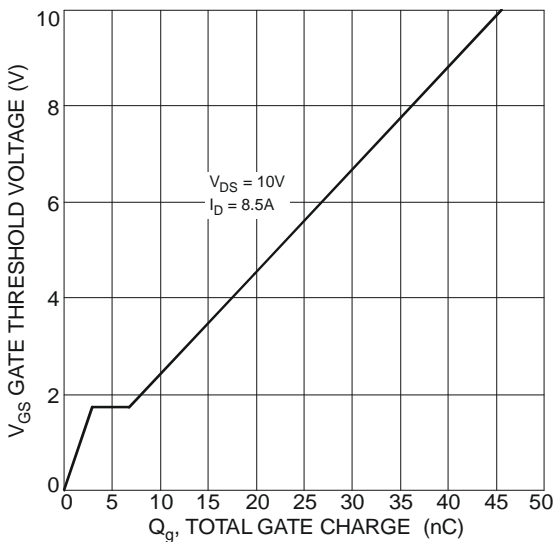


Fig. 11 Gate Charge

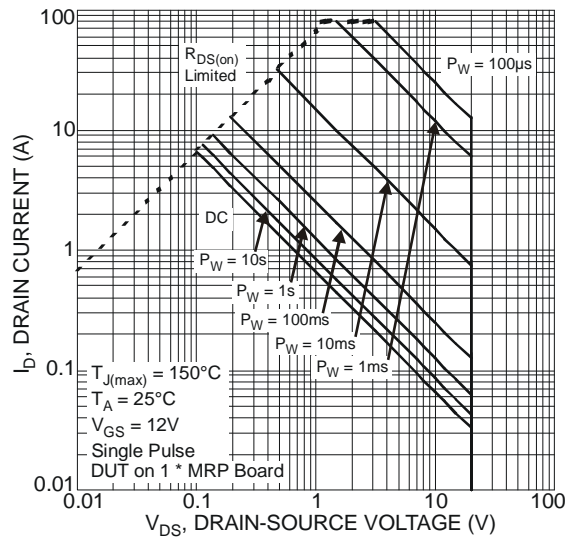
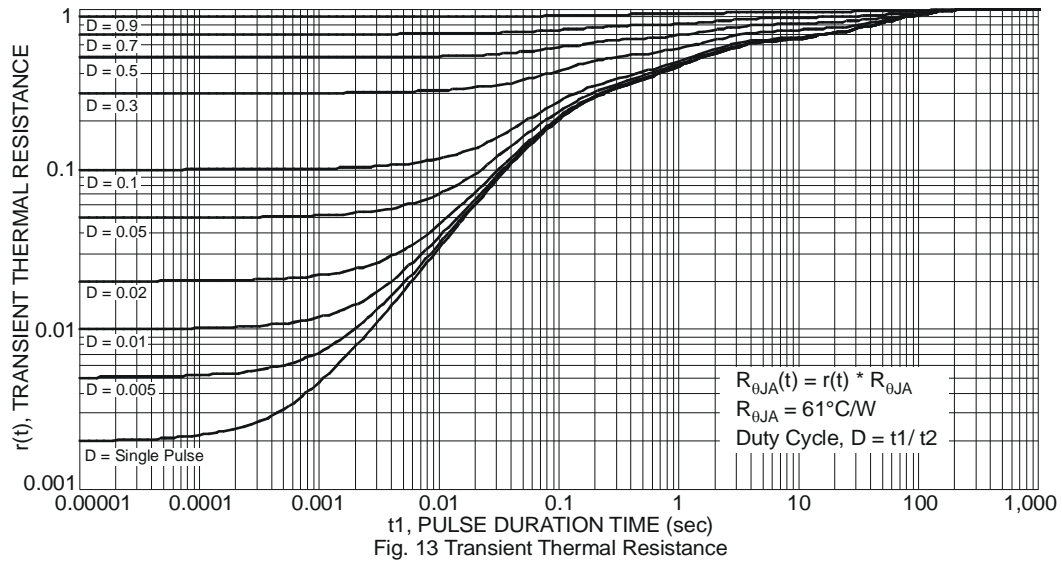
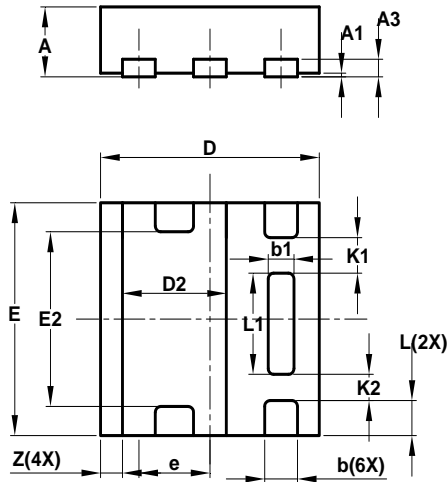


Fig. 12 SOA, Safe Operation Area



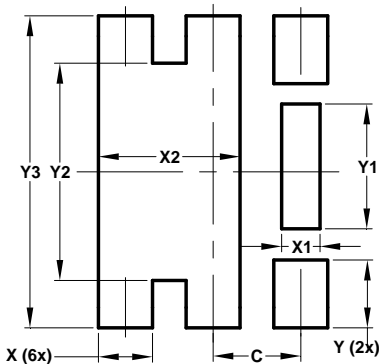
**Package Outline Dimensions**



U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20

All Dimensions in mm

**Suggested Pad Layout**



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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- Консультации по применению компонента;
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- Техническая поддержка проекта;
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**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.